
Supporting information

Solution-processable zinc oxide nanorods and reduced graphene oxide hybrid nanostructure for highly flexible and stable memristor

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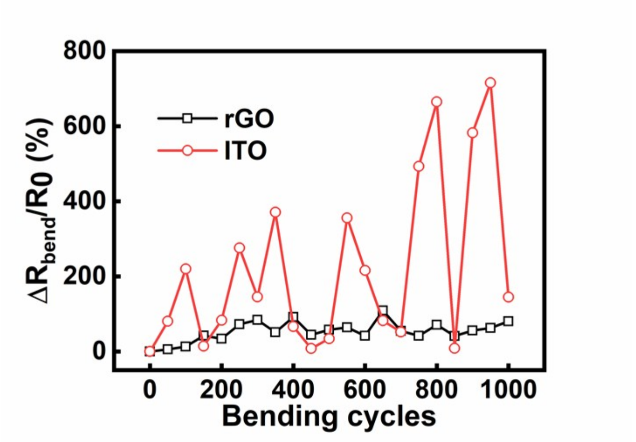

Figure S1. The dependence of sheet resistance on bending cycles for rGO thin film (black line) and ITO electrodes (red line).

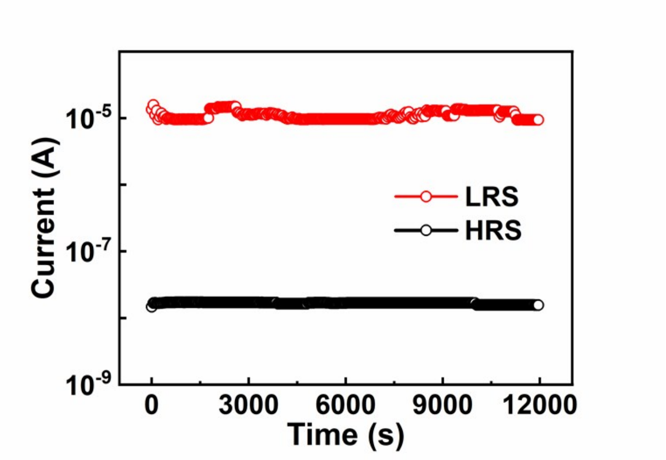

Figure S2. Retention of the memristor underwent bending cycles up to 1000.